

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOS V)

2SK2967

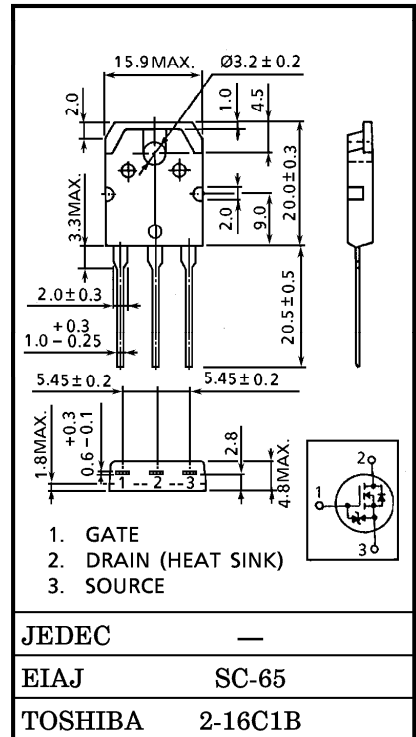
HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 48 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 30 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 250 \text{ V}$)
- Enhancement-Model : $V_{th} = 1.5 \sim 3.5 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	250	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	250	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	30 A
	Pulse	I_{DP}	120 A
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	150	W
Single Pulse Avalanche Energy*	E_{AS}	925	mJ
Avalanche Current	I_{AR}	30	A
Repetitive Avalanche Energy**	E_{AR}	15	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight : 4.6 g (Typ.)

HERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ\text{C/W}$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ\text{C/W}$

Note ;

* $V_{DD} = 50 \text{ V}$, $T_{ch} = 25^\circ\text{C}$, $L = 1.74 \text{ mH}$, $I_{AR} = 30 \text{ A}$, $R_G = 25 \Omega$

** Repetitive rating ; Pulse Width Limited by Max. junction temperature.

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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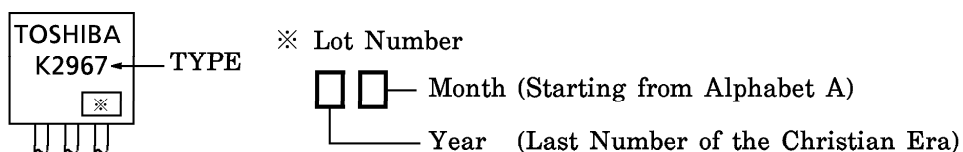
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

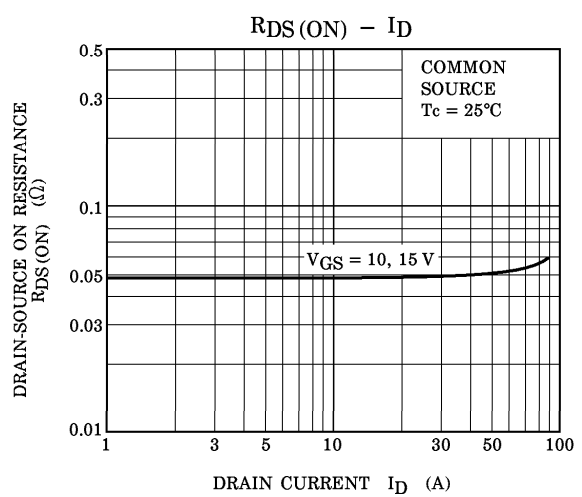
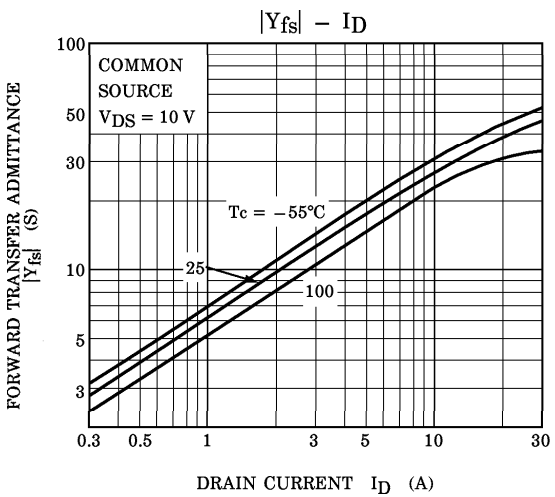
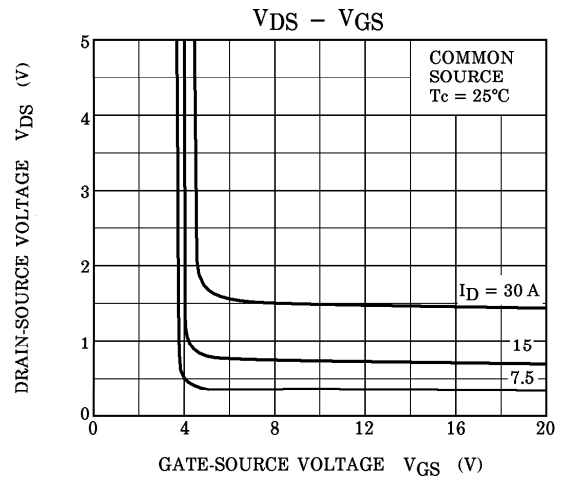
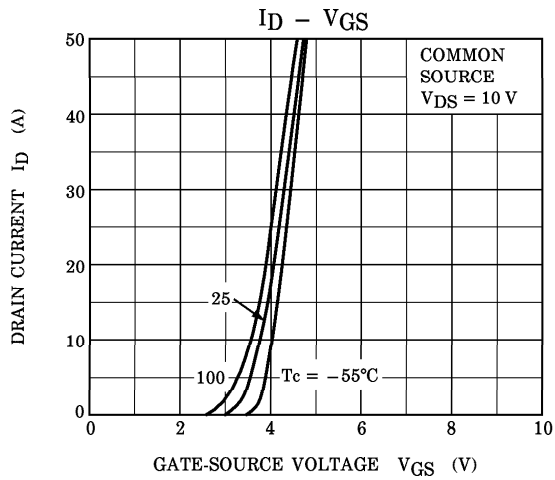
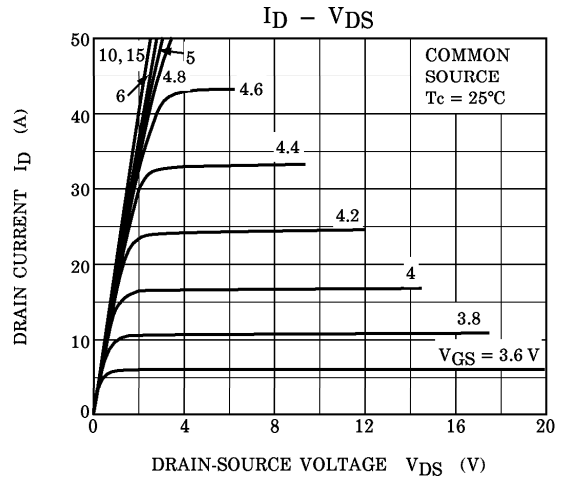
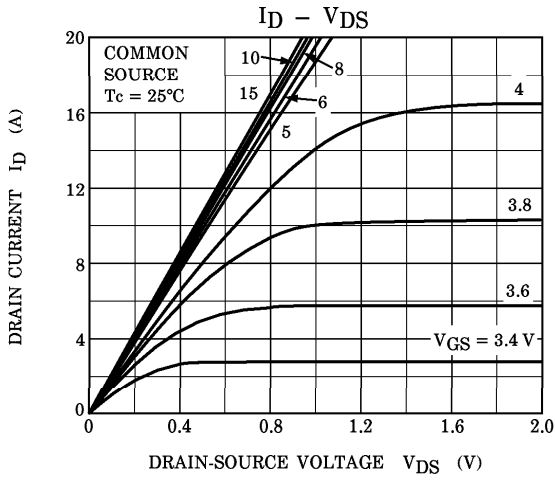
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±16 V, VDS = 0 V	—	—	±10	μA
Drain Cut-off Current		IDSS	VDS = 250 V, VGS = 0 V	—	—	100	μA
Drain-Source Breakdown Voltage		V(BR)DSS	ID = 10 mA, VGS = 0 V	250	—	—	V
Gate Threshold Voltage		Vth	VDS = 10 V, ID = 1 mA	1.5	—	3.5	V
Drain-Source ON Resistance		RDS(ON)	VGS = 10 V, ID = 15 A	—	48	68	mΩ
Forward Transfer Admittance		Yfs	VDS = 10 V, ID = 15 A	15	30	—	S
Input Capacitance		Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz	—	5400	—	pF
Reverse Transfer Capacitance		Crss		—	580	—	
Output Capacitance		Coss		—	1900	—	
Switching Time	Rise Time	tr	<p> $I_D = 15\text{ A}$ $V_{GS} = 10\text{ V}$ $V_{DD} \doteq 100\text{ V}$ $R_L = 6.7\ \Omega$ $V_{IN} : t_r, t_f < 5\text{ ns}$ $\text{Duty} \leq 1\%$, $t_w = 10\ \mu\text{s}$ </p>	—	20	—	ns
	Turn-on Time	ton		—	50	—	
	Fall Time	tf		—	35	—	
	Turn-off Time	t _{off}		—	200	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 200 V, VGS = 10 V ID = 30 A	—	132	—	nC
Gate-Source Charge		Qgs		—	80	—	
Gate-Drain (“Miller”) Charge		Qgd		—	52	—	

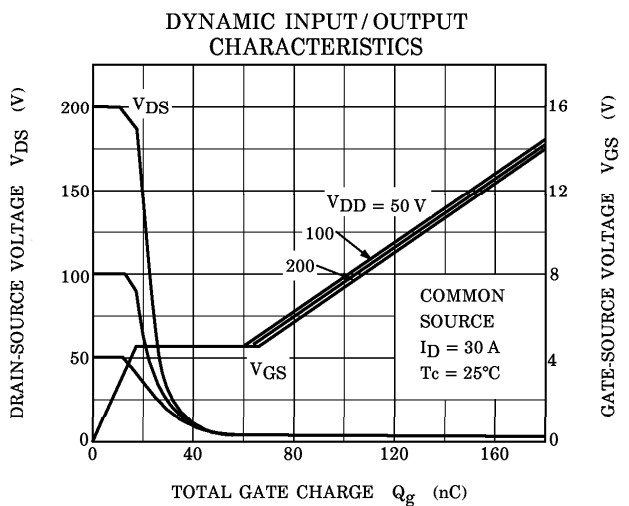
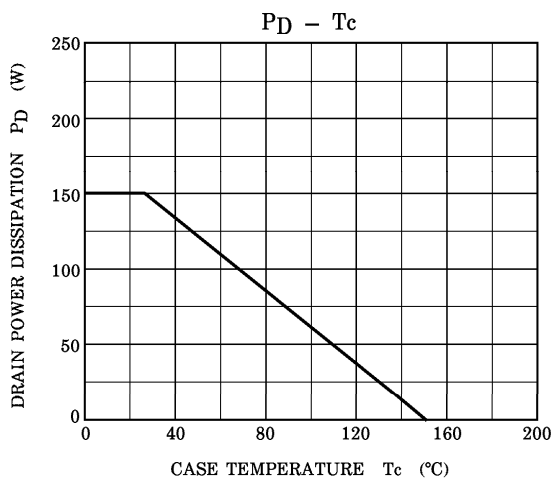
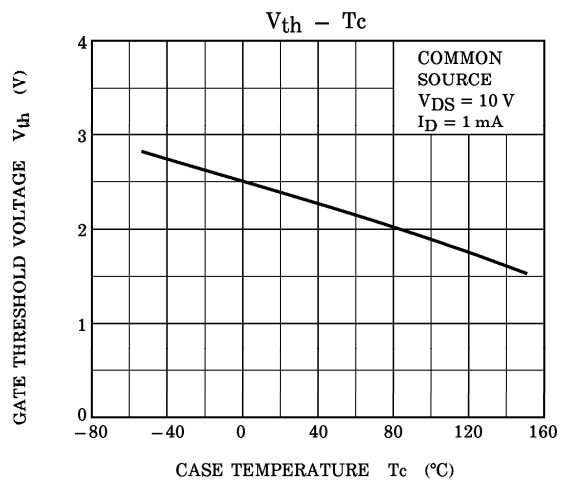
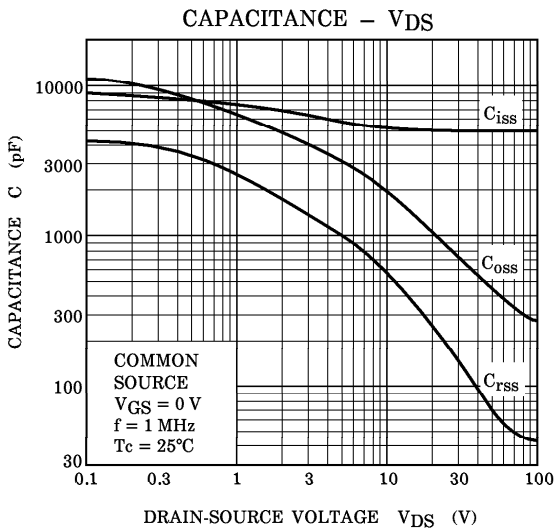
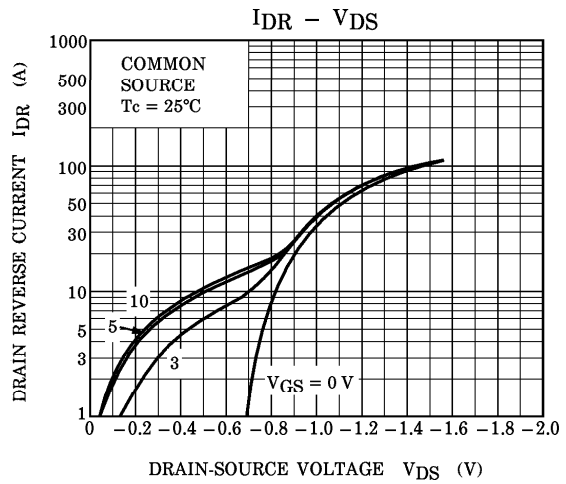
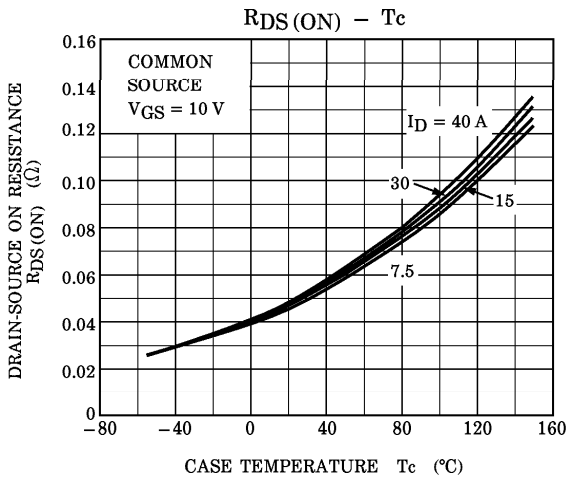
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

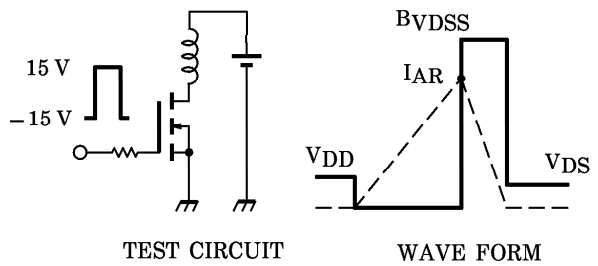
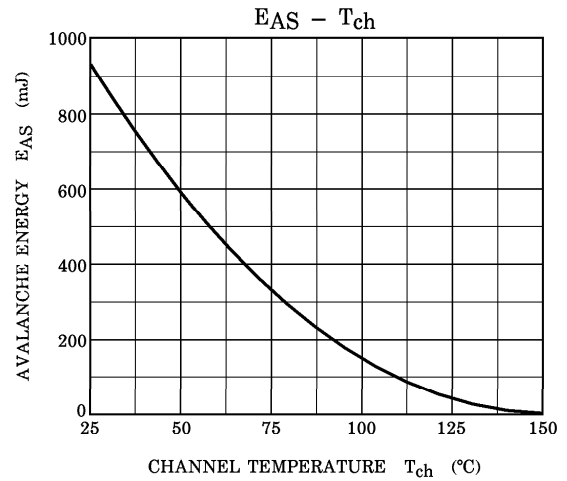
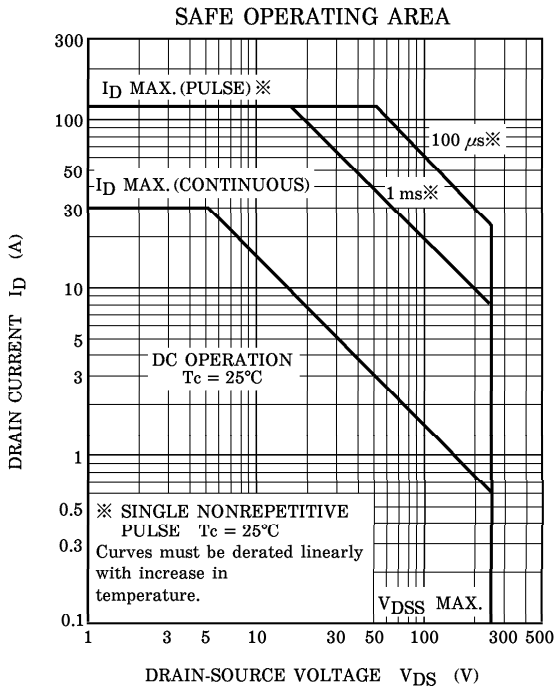
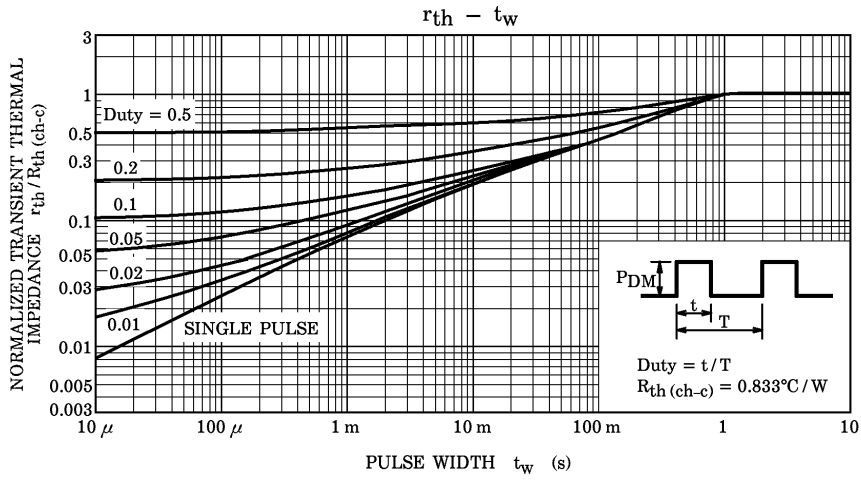
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	30	A
Pulse Drain Reverse Current	IDRP	—	—	—	120	A
Diode Forward Voltage	VDSF	IDR = 30 A, VGS = 0 V	—	—	−2.0	V
Reverse Recovery Time	t _{rr}	IDR = 30 A, VGS = 0 V	—	270	—	ns
Reverse Recovery Charge	Q _{rr}	dIDR / dt = 100 A / μs	—	3.0	—	μC

MARKING









Peak $I_{AR} = 30 A$, $R_G = 25 \Omega$
 $V_{DD} = 50 V$, $L = 1.74 mH$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$